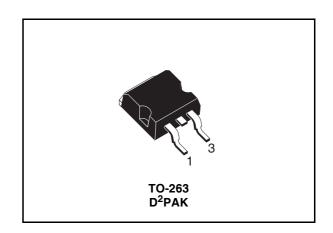


BULB49DT4

High voltage fast-switching NPN power transistor

General features

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed
- High ruggedness
- Surface mounting TO-263 (D²PAK) power package
- In compliance with the 2002/93/EC European Directive



Description

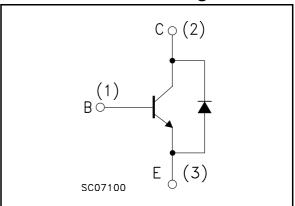
The device is manufactured using high voltage Multi-Epitaxial Planar technology for high switching speeds and high voltage capability.

The device is designed for use in electronic transformer for halogen lamps.

Applications

- Electronic transformers for halogen lamps
- Flyback and forward single transistor low power converters

Internal schematic diagrams



Order codes

Part Number	Marking	Package	Packing
BULB49DT4	BULB49D	D ² PAK	Tape & reel

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BULB49DT4 Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} =0)	850	V
V _{CEO}	Collector-emitter voltage (I _B =0)	450	٧
V _{EBO}	Emitter-base voltage ($I_C = 0$, $I_B < 2A$, $t_P < 10ms$)	V _{(BR)EBO}	V
I _C	Collector current	5	Α
I _{CM}	Collector peak current (t _P < 5ms)	10	Α
I _B	Base current	2	Α
I _{BM}	Base peak current (t _P < 5ms)	4	Α
P _{tot}	Total dissipation at T _c ≤ 25°C	80	W
T _{stg}	Storage temperature	-65 to 150	°C
TJ	Max. operating junction temperature	150	°C

Table 2. Thermal data

Symbol	Parameter	Value	Unit	
R _{thj-case}	Thermal resistance junction-case	max	1.56	°C/W
R _{thj-amb}	Thermal resistance junction-ambient	max	62.5	°C/W

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Electrical characteristics BULB49DT4

2 Electrical characteristics

(T_{case} = 25°C unless otherwise specified)

Table 3. Electrical characteristics

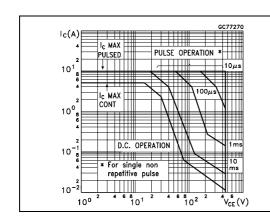
Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector cut-off current (V _{BE} =0)	$V_{CE} = 850V$ $V_{CE} = 850V$ $T_j = 125^{\circ}C$			100 500	μ Α μ Α
I _{EBO}	Emitter cut-off current (I _C =0)	V _{EB} = 9V			100	μΑ
V _{(BR)EBO}	Emitter-base brakdown voltage (I _C = 0)	I _E =10mA	10		18	V
V _{CEO(sus)} ⁽¹⁾	Collector-emitter sustaining voltage (I _B = 0)	I _C =10mA	450			V
V _{CE(sat)} (1)	Collector-emitter saturation voltage			0.1	0.3 0.6 1.2	V V V
V _{BE(sat)} (1)	Base-emitter saturation voltage				1 1.3	V V
h _{FE} ⁽¹⁾	DC current gain	$\begin{split} & I_{\text{C}} = 10 \text{mA} & V_{\text{CE}} = 5 \text{V} \\ & I_{\text{C}} = 500 \text{mA} & V_{\text{CE}} = 5 \text{V} \\ & I_{\text{C}} = 7 \text{A} & V_{\text{CE}} = 10 \text{V} \end{split}$	10		60 10	
V _{CEW} ⁽¹⁾	Maximum collector- emitter voltage without snubber	I_{C} =8A V_{BB} = -2.5V L =50 μ H R_{BB} =0 t_{p} =10 μ s	450			V
t _s	Resistive load Storage time Fall time	$V_{CC} = 250V$ $I_{C} = 2A$ $I_{B1} = I_{B2} = 400 \text{mA}$ $I_{p} = 30 \mu \text{s}$ (see figure 11)	2		3 0.8	μs μs
t _s	Inductive load Storage time Fall time	V_{CL} = 300V I_{C} = 4A $I_{B(on)}$ = 800mA $I_{BB(off)}$ = 0 $I_{BE(off)}$ = -5V I_{C} = 1mH (see figure 12)		0.5 50	1.3 100	μs ns
V_{F}	Diode forward voltage	$I_C = 3A$			1.5	V

Note (1) Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

Figure 2. Derating current



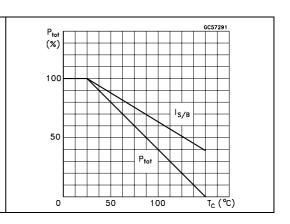
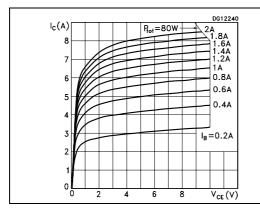


Figure 3. Output characteristics

Figure 4. Collector-emitter saturation voltage



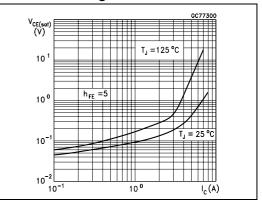
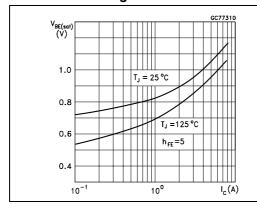
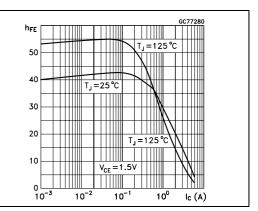


Figure 5. Base-emitter saturation voltage

Figure 6. DC current gain

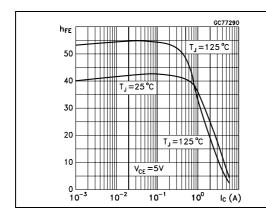




Electrical characteristics BULB49DT4

Figure 7. DC current gain

Figure 8. Inductive load storage time



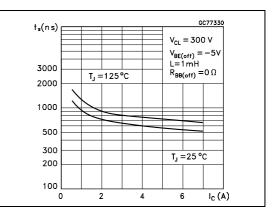
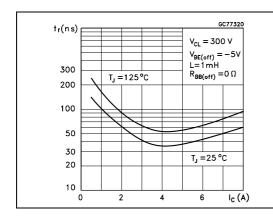
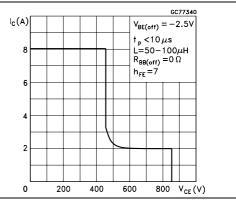


Figure 9. Inductive load fall time

Figure 10. Reverse biased safe operating area





2.2 Test circuits

Figure 11. Resistive load switching test circuit

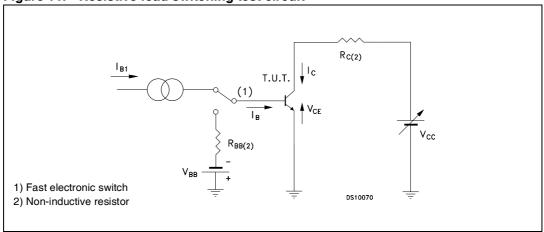
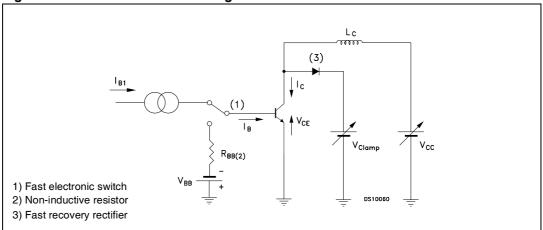


Figure 12. Inductive load switching test circuit

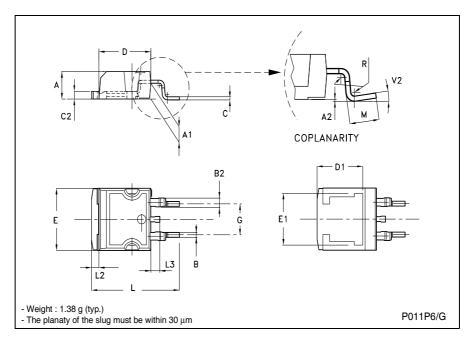


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-263 (D²PAK) MECHANICAL DATA

DIM.		mm		inch	inch	
DIW.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.40		4.60	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.70		0.93	0.027		0.036
B2	1.14		1.70	0.044		0.067
С	0.45		0.60	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8.00			0.315	
Е	10.00		10.40	0.393		0.409
E1		8.50			0.334	
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.4	0.050		0.055
L3	1.40		1.75	0.055		0.068
М	2.40		3.2	0.094		0.126
R		0.40			0.016	
V2	0°		8°	0°		8°



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Revision history BULB49DT4

4 Revision history

Table 4. Revision history

Date	Revision	Changes
10-Sep-2003	1	First release.
21-Jul-2006	2	New template

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